

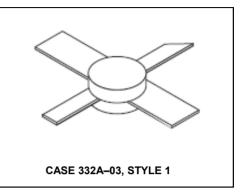
Rev. V1

### Microwave Pulse Power Silicon NPN Transistor 4.0W (peak), 960–1215MHz

Designed for Class B and C common base amplifier applications in short and long pulse TACAN, IFF, DME, and radar transmitters.

- Guaranteed performance @ 1090 MHz, 35 Vdc Output power = 4.0 W Peak Minimum gain = 10 dB
- 100% Tested for load mismatch at all phase angles with 10:1 VSWR
- Industry standard package
- Nitride passivated
- Gold metallized, emitter ballasted for long life and resistance to metal migration
- Internal input matching for broadband operation





#### MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V <sub>CEO</sub>	20	Vdc
Collector-Base Voltage	V <sub>CBO</sub>	50	Vdc
Emitter-Base Voltage	V <sub>EBO</sub>	3.5	Vdc
Collector Current — Continuous	IC	250	mAdc
Total Device Dissipation @ T <sub>C</sub> = 25°C (1) Derate above 25°C	PD	7.0 40	Watts mW/°C
Storage Temperature Range	T <sub>stg</sub>	-65 to +150	°C
THERMAL CHARACTERISTICS			·

Characteristic	Symbol	Мах	Unit
Thermal Resistance, Junction to Case (2)	R <sub>eJC</sub>	25	°C/W
-			,

ELECTRICAL CHARACTERISTICS (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Тур	Мах	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage (I <sub>C</sub> = 5.0 mAdc, I <sub>B</sub> = 0)	V <sub>(BR)CEO</sub>	20	-	-	Vdc
Collector–Emitter Breakdown Voltage $(I_C = 5.0 \text{ mAdc}, V_{BE} = 0)$	V <sub>(BR)CES</sub>	50	-	-	Vdc
Collector–Base Breakdown Voltage (I <sub>C</sub> = 5.0 mAdc, I <sub>E</sub> = 0)	V <sub>(BR)CBO</sub>	50	-	-	Vdc
Emitter–Base Breakdown Voltage (I <sub>E</sub> = 1.0 mAdc, I <sub>C</sub> = 0)	V <sub>(BR)EBO</sub>	3.5	-	-	Vdc
Collector Cutoff Current ( $V_{CB} = 35 \text{ Vdc}, I_E = 0$ )	I <sub>CBO</sub>	-	-	0.5	mAdc
ON CHARACTERISTICS					
DC Current Gain	hee	10		100	

DC Current Gain	h <sub>FE</sub>	10	_	100	
(I <sub>C</sub> = 75 mAdc, V <sub>CE</sub> = 5.0 Vdc)					

NOTES:

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(continued)

1. These devices are designed for RF operation. The total device dissipation rating applies only when the device is operated as RF amplifiers. 2. Thermal Resistance is determined under specified RF operating conditions by infrared measurement techniques.

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Characteristic	Symbol	Min	Тур	Мах	Unit
DYNAMIC CHARACTERISTICS					
Output Capacitance ( $V_{CB}$ = 35 Vdc, I <sub>E</sub> = 0, f = 1.0 MHz)	C <sub>ob</sub>	_	3.3	5.0	pF
FUNCTIONAL TESTS (Pulse Width = 10 μs, Duty Cycle = 1.0%)					
Common–Base Amplifier Power Gain (V <sub>CC</sub> = 35 Vdc, P <sub>out</sub> = 4.0 W pk, f = 1090 MHz)	G <sub>PB</sub>	10	11	—	dB
Collector Efficiency (V <sub>CC</sub> = 35 Vdc, P <sub>out</sub> = 4.0 W pk, f = 1090 MHz)	η	40	45	—	dB
Load Mismatch (V <sub>CC</sub> = 35 Vdc, P <sub>out</sub> = 4.0 W pk, f = 1090 MHz, VSWR = 10:1 All Phase Angles)	Ψ	No	Degradation	in Power Outp	out

#### n V<sub>CC</sub> = 35 Vdc 0 C3 ; C1 C2 7 L2 RF RF Z2 Z4 Z6 Z1 Z5 Z3 INPUT A OUTPUT Ċ4 D.U.T. L1

 $\begin{array}{l} C1 \longrightarrow 0.1 \ \mu\text{F} \\ C2, \ C4 \longrightarrow 220 \ \text{pF} \ \text{Chip} \ \text{Capacitor} \\ C3 \longrightarrow 20 \ \mu\text{F}, \ 50 \ \text{V} \ \text{Electrolytic} \\ L1, \ L2 \longrightarrow 3 \ \text{Turns} \ \#18 \ \text{AWG}, \ 1/8'' \ \text{ID} \\ \text{Z1-Z6} \ \text{Distributed} \ \text{Microstrip} \ \text{Elements}, \ \text{See} \ \text{Photomaster} \end{array}$ 

Board Material - 0.031" Thick Glass Teflon

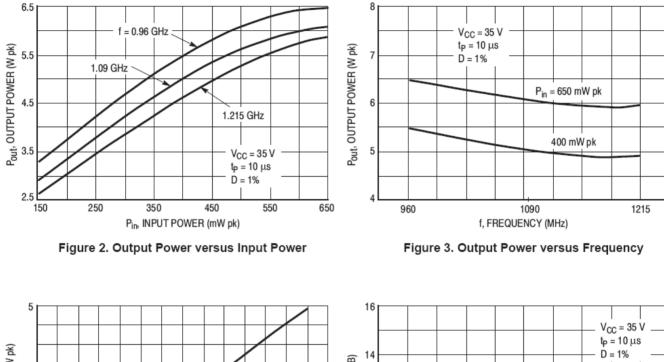
Figure 1, 1090 MHz Test Circuit

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#### **TYPICAL CHARACTERISTICS**

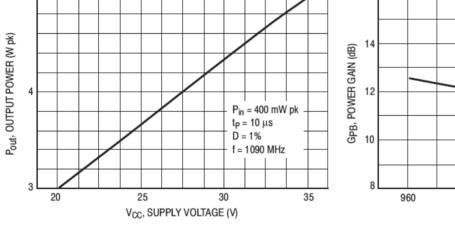


Figure 4. Output Power versus Supply Voltage

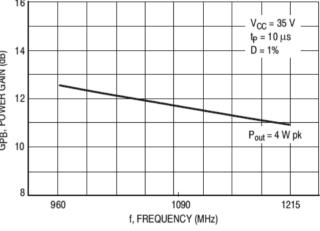


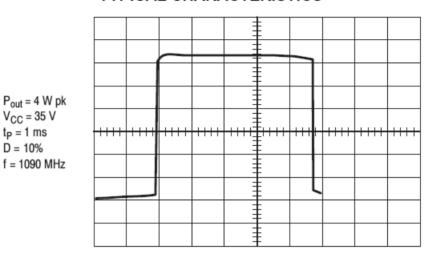
Figure 5. Power Gain versus Frequency

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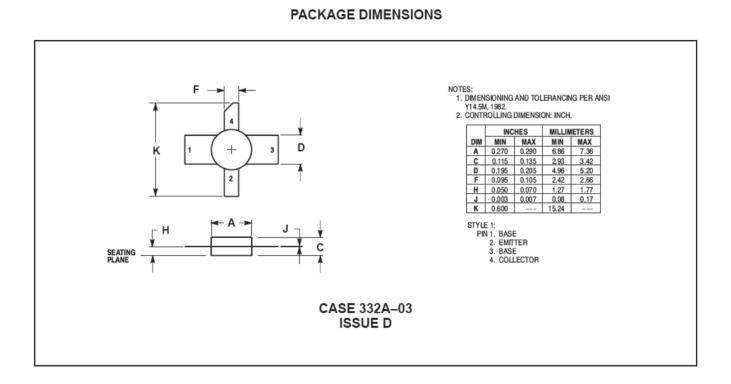
#### **TYPICAL CHARACTERISTICS**

Figure 7. Typical Long Pulse Performance



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